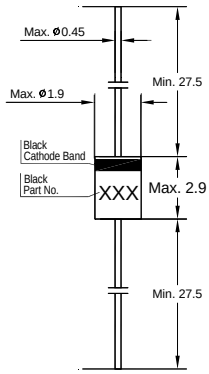
RB441Q-40

SILICON EPITAXIAL PLANAR TYPE SCHOTTKY BARRIER DIODES

for low current rectification



Glass Case DO-34
Dimensions in mm

Features

- Low forward rise voltage (V_F)
- Small pitch enables insertion on PCBs
- Glass sealed envelope for high reliability

Absolute Maximum Ratings (T_a = 25 °C)

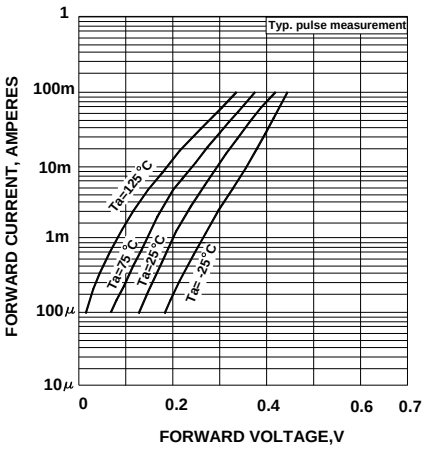
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	100	mA
Peak Forward Surge Current	I_{FSM}	1	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{Stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

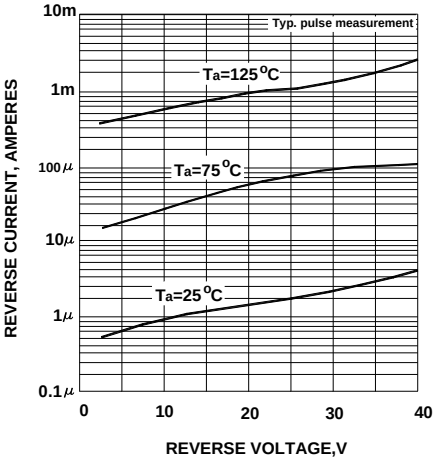
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 10 mA at I_F = 100 mA	V_F	- -	0.34 0.55	V
Reverse Current at V_R = 40 V	I_R	-	100	µA
Terminal Capacitance at V_R = 10 V, f = 1 MHz	C_T	6	-	pF

Dated : 25/06/2007

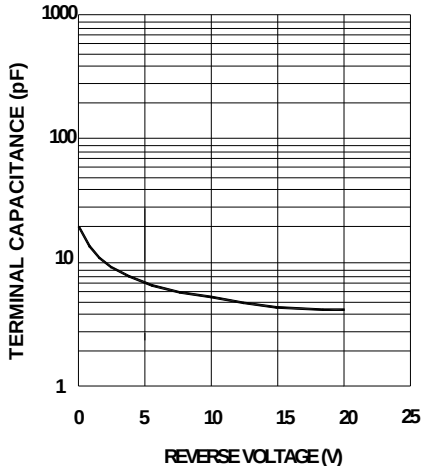
FORWARD CHARACTERISTICS



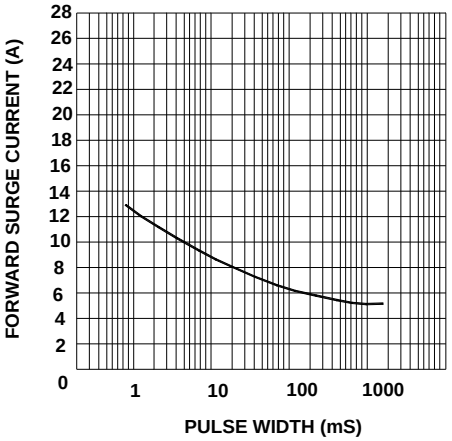
REVERSE CHARACTERISTICS



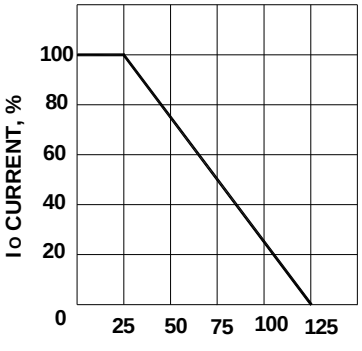
TERMINAL CAPACITANCE CHARACTERISTICS



FORWAR SURGE CURRENT CHARACTERISTIC



DERATING CURVE
(mounting on glass epoxy PCBs)



MEAN RECTIFYING CURRENT
CHARACTERISTICS